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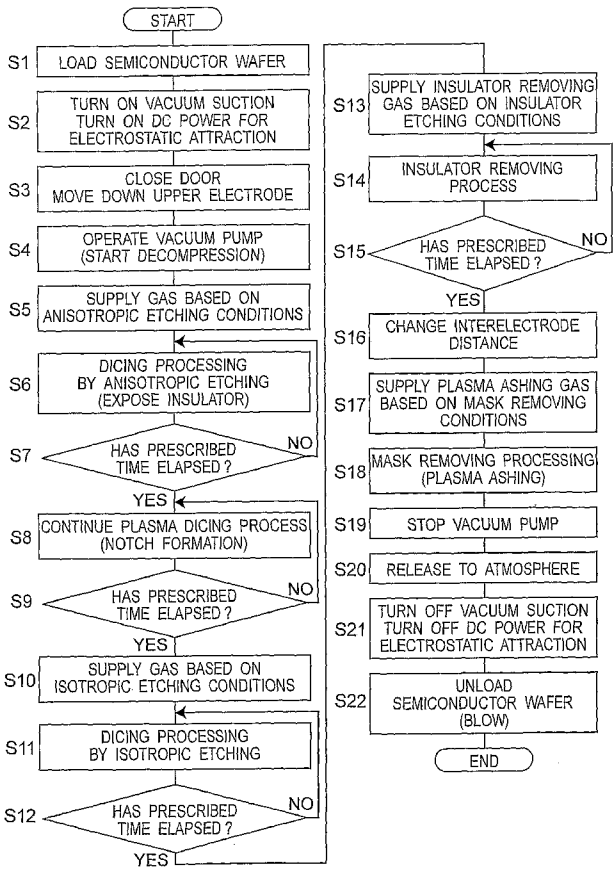
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(54) Title: MANUFACTURING METHOD FOR SEMICONDUCTOR CHIPS, AND SEMICONDUCTOR CHIP



(57) Abstract: In a manufacturing method for performing plasma etching on a second surface of a semiconductor wafer that has a first surface where an insulating film is placed in dividing regions and the second surface which is opposite from the first surface and on which a mask for defining the dividing regions is placed thereby exposing the insulating film from etching bottom portions by removing portions that correspond to the dividing regions and subsequently continuously performing the plasma etching in the state in which the exposed surfaces of the insulating film are charged with electric charge due to ions in the plasma thereby removing corner portions put in contact with the insulating film in the device-formation-regions, isotropic etching is performed on the semiconductor wafer at any timing.

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